Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

MJW21195 (PNP)
MJW21196 (NPN)

Silicon Power Transistors

The MJW21195 and MJW21196 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

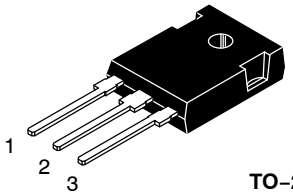
Features

- Total Harmonic Distortion Characterized
- High DC Current Gain – h_{FE} = 20 Min @ I_C = 8 Adc
- Excellent Gain Linearity
- High SOA: 2.25 A, 80 V, 1 Second
- Pb−Free Packages are Available*

ON Semiconductor®

http://onsemi.com

16 AMPERES
COMPLEMENTARY
SILICON POWER TRANSISTORS
250 VOLTS, 200 WATTS



TO−247
CASE 340L

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	250	Vdc
Collector−Base Voltage	V_{CBO}	400	Vdc
Emitter−Base Voltage	V_{EBO}	5.0	Vdc
Collector−Emitter Voltage – 1.5 V	V_{CEX}	400	Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	16 30	Adc
Base Current – Continuous	I_B	5.0	Adc
Total Power Dissipation @ T_C = 25°C Derate Above 25°C	P_D	200 1.43	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

THERMAL CHARACTERISTICS

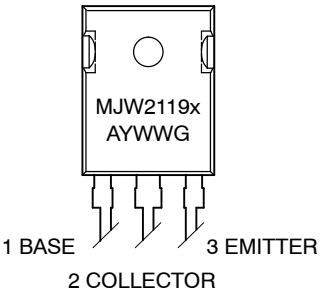
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	0.7	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	40	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 μs, Duty Cycle ≤ 10%.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



x = 5 or 6
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJW21195	TO−247	30 Units/Rail
MJW21195G	TO−247 (Pb−Free)	30 Units/Rail
MJW21196	TO−247	30 Units/Rail
MJW21196G	TO−247 (Pb−Free)	30 Units/Rail

© Semiconductor Components Industries, LLC, 2010

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS						
Collector−Emitter Sustaining Voltage (I_C = 100 mAdc, I_B = 0)		$V_{CEO(sus)}$	250	–	–	Vdc
Collector Cutoff Current (V_{CE} = 200 Vdc, I_B = 0)		I_{CEO}	–	–	100	μAdc
Emitter Cutoff Current (V_{CE} = 5 Vdc, I_C = 0)		I_{EBO}	–	–	50	μAdc
Collector Cutoff Current (V_{CE} = 250 Vdc, $V_{BE(off)}$ = 1.5 Vdc)		I_{CEX}	–	–	50	μAdc
SECOND BREAKDOWN						
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 50 Vdc, t = 1 s (non−repetitive)) (V_{CE} = 80 Vdc, t = 1 s (non−repetitive))		$I_{S/b}$	 4.0 2.25	 – –	 – –	Adc
ON CHARACTERISTICS						
DC Current Gain (I_C = 8 Adc, V_{CE} = 5 Vdc) (I_C = 16 Adc, I_B = 5 Adc)		h_{FE}	 20 8	 – –	 80 –	
Base−Emitter On Voltage (I_C = 8 Adc, V_{CE} = 5 Vdc)		$V_{BE(on)}$	–	–	2.0	Vdc
Collector−Emitter Saturation Voltage (I_C = 8 Adc, I_B = 0.8 Adc) (I_C = 16 Adc, I_B = 3.2 Adc)		$V_{CE(sat)}$	 – –	 – –	 1.0 3	Vdc
DYNAMIC CHARACTERISTICS						
Total Harmonic Distortion at the Output V_{RMS} = 28.3 V, f = 1 kHz, P_{LOAD} = 100 W_{RMS} (Matched pair h_{FE} = 50 @ 5 A/5 V)	h_{FE} unmatched h_{FE} matched	T_{HD}	 – –	 0.8 0.08	 – –	%
Current Gain Bandwidth Product (I_C = 1 Adc, V_{CE} = 10 Vdc, f_{test} = 1 MHz)		f_T	4	–	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f_{test} = 1 MHz)		C_{ob}	–	–	500	pF

TYPICAL CHARACTERISTICS

PNP MJW21195

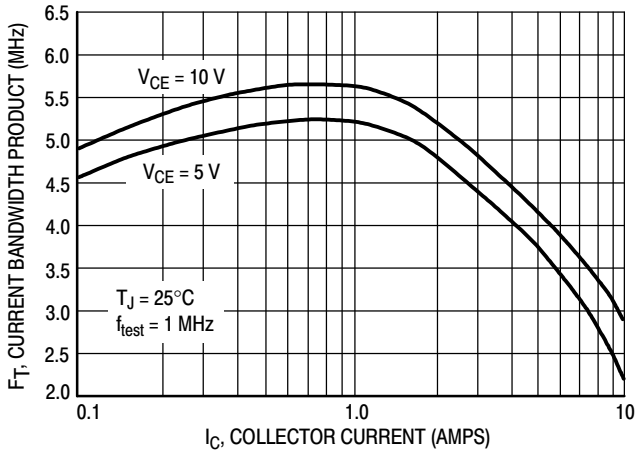


Figure 1. Typical Current Gain Bandwidth Product

NPN MJW21196

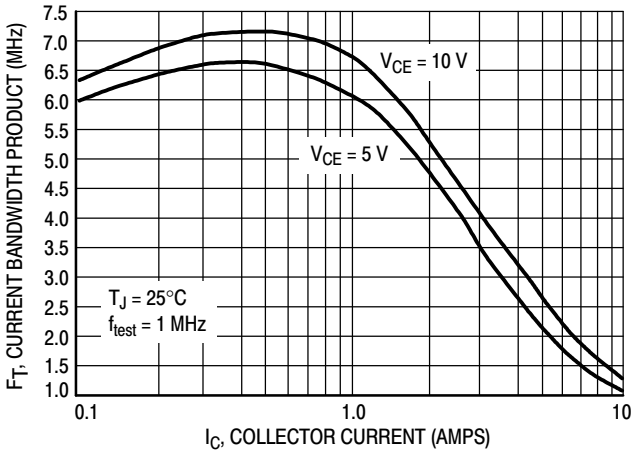


Figure 2. Typical Current Gain Bandwidth Product

PNP MJW21195

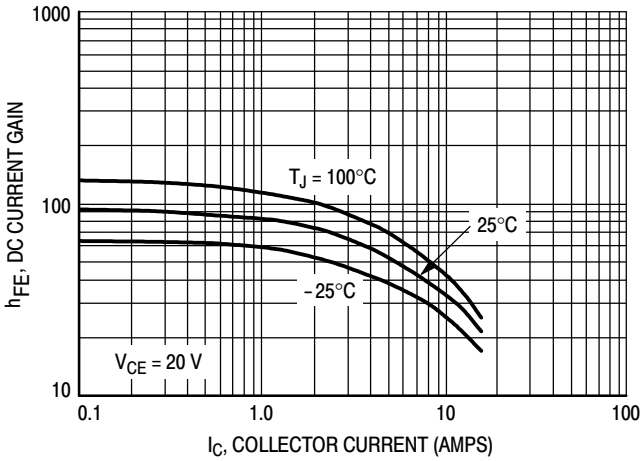


Figure 3. DC Current Gain, V_{CE} = 20 V

NPN MJW21196

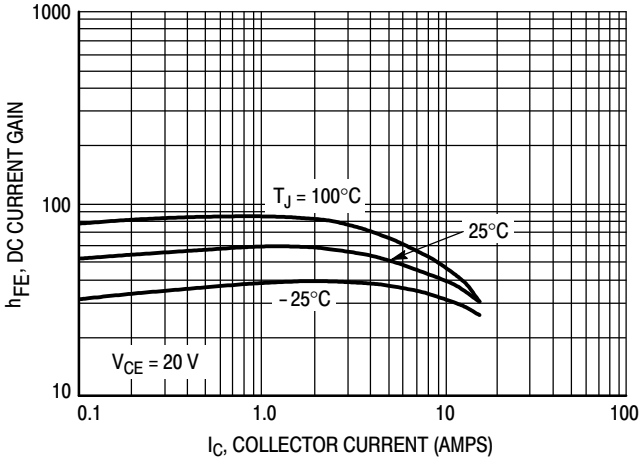


Figure 4. DC Current Gain, V_{CE} = 20 V

PNP MJW21195

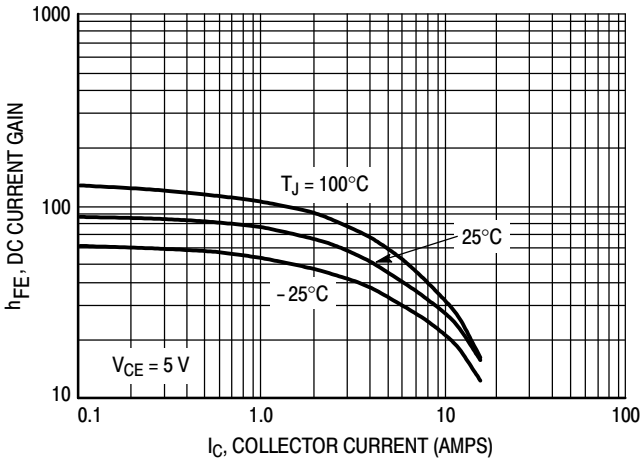


Figure 5. DC Current Gain, V_{CE} = 5 V

NPN MJW21196

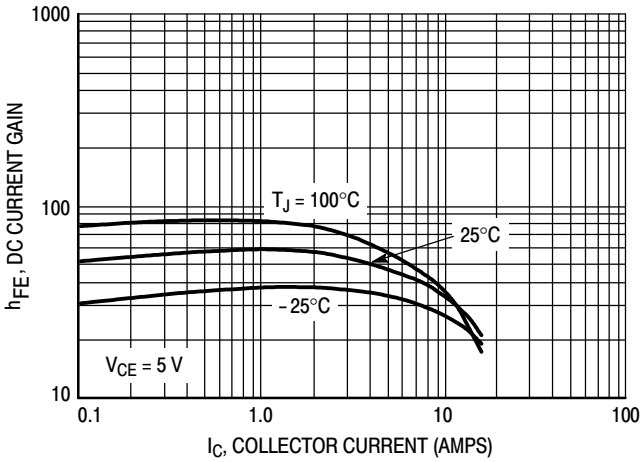


Figure 6. DC Current Gain, V_{CE} = 5 V

TYPICAL CHARACTERISTICS

PNP MJW21195

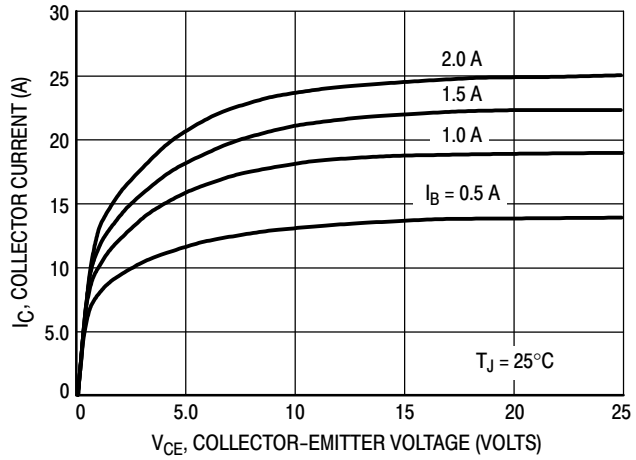


Figure 7. Typical Output Characteristics

NPN MJW21196

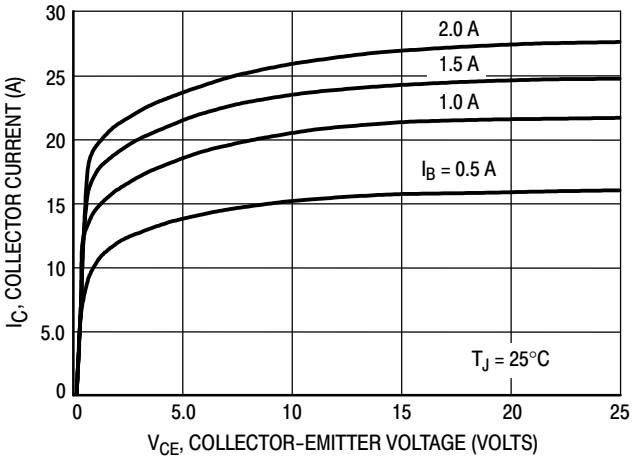


Figure 8. Typical Output Characteristics

PNP MJW21195

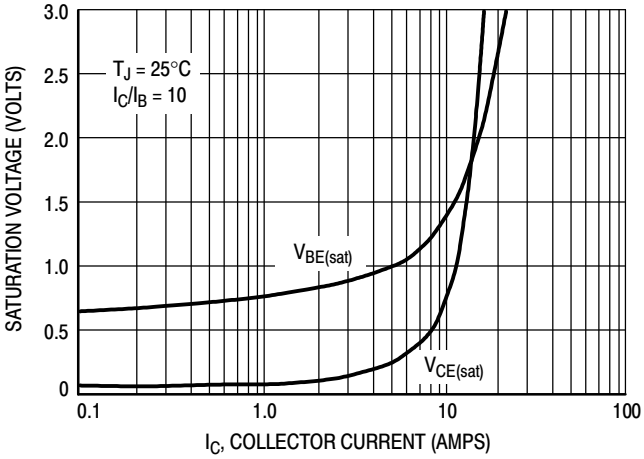


Figure 9. Typical Saturation Voltages

NPN MJW21196

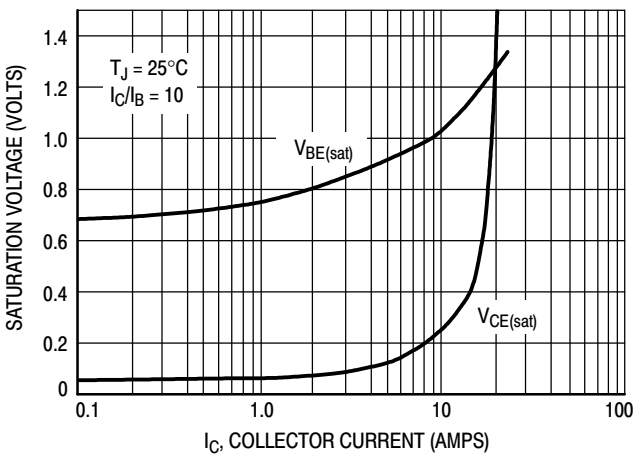


Figure 10. Typical Saturation Voltages

PNP MJW21195

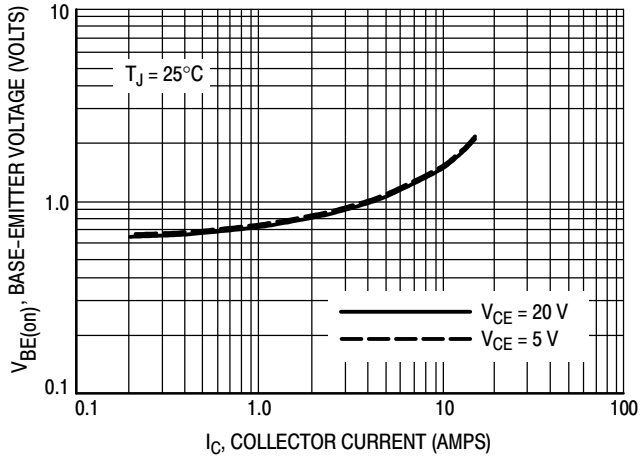


Figure 11. Typical Base−Emitter Voltage

NPN MJW21196

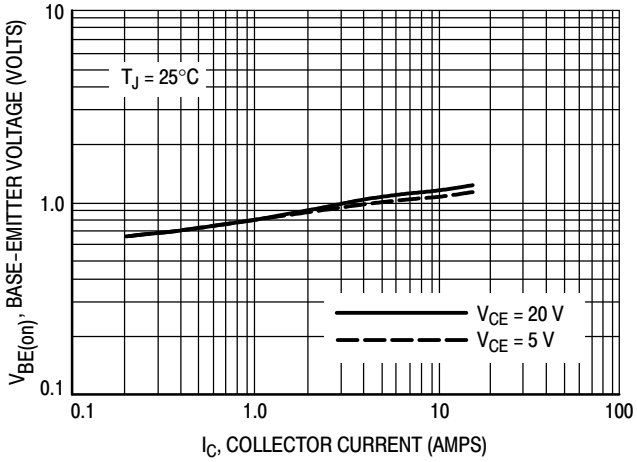


Figure 12. Typical Base−Emitter Voltage

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

TYPICAL CHARACTERISTICS

PNP MJW21195

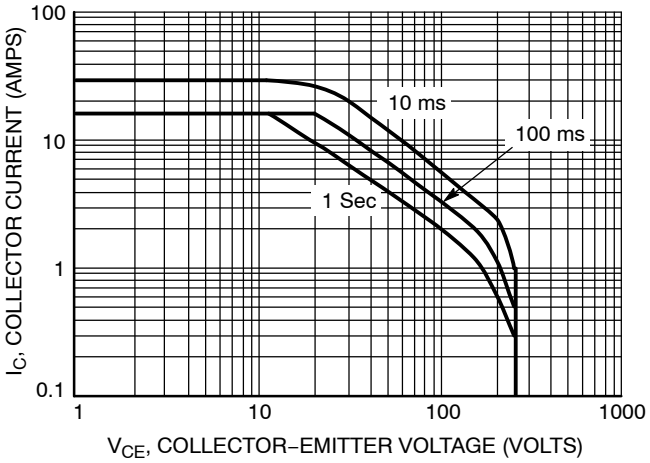


Figure 13. Active Region Safe Operating Area

NPN MJW21196

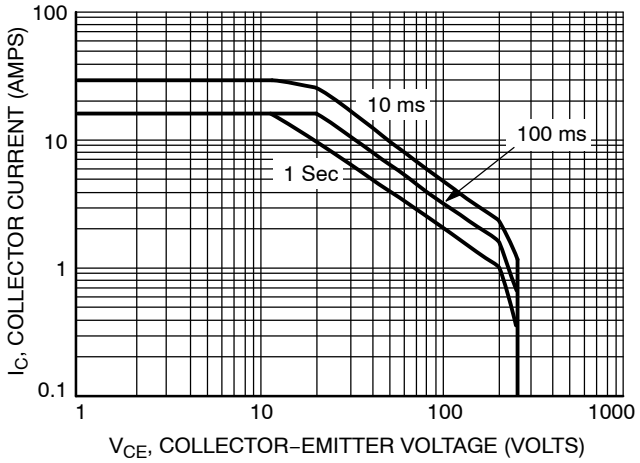


Figure 14. Active Region Safe Operating Area

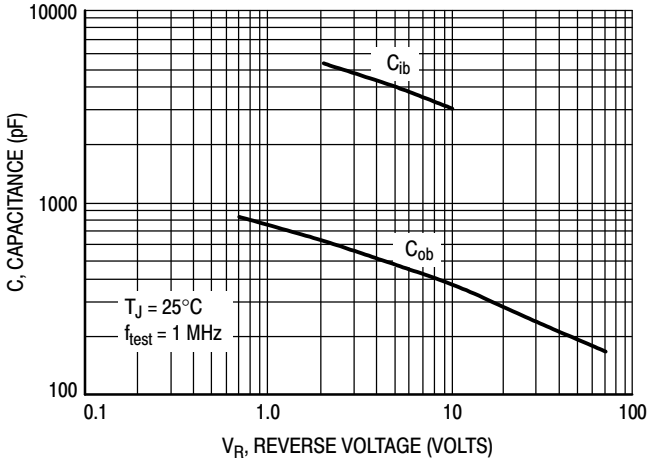


Figure 15. MJW21195 Typical Capacitance

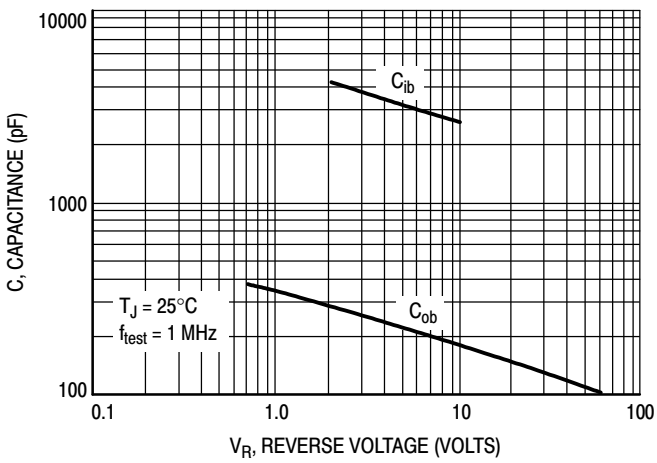


Figure 16. MJW21196 Typical Capacitance

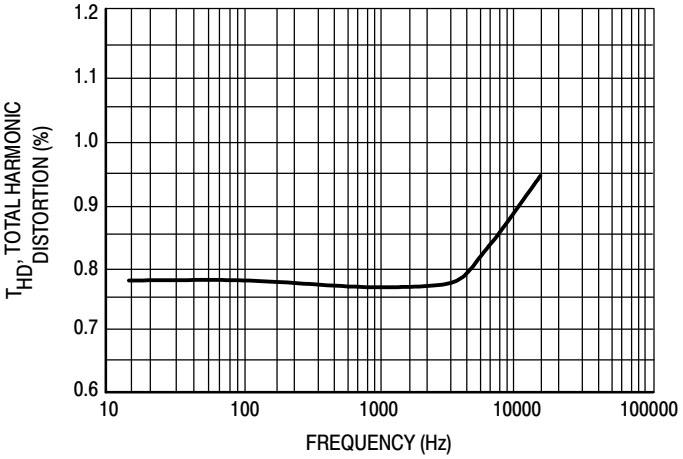


Figure 17. Typical Total Harmonic Distortion

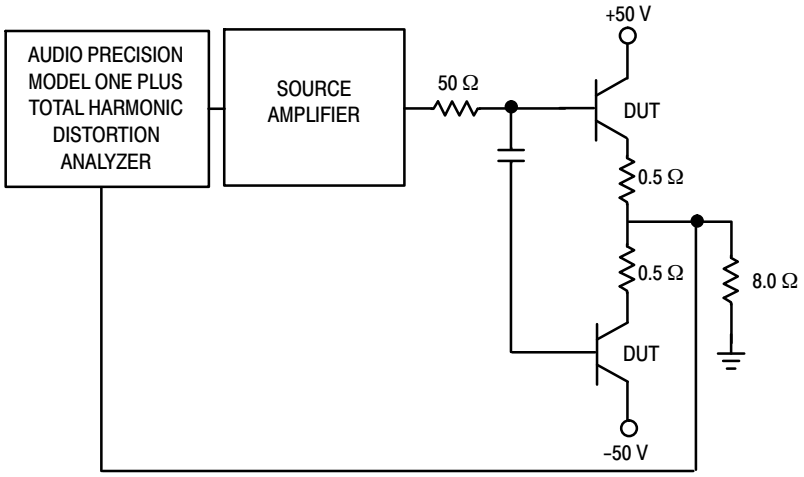
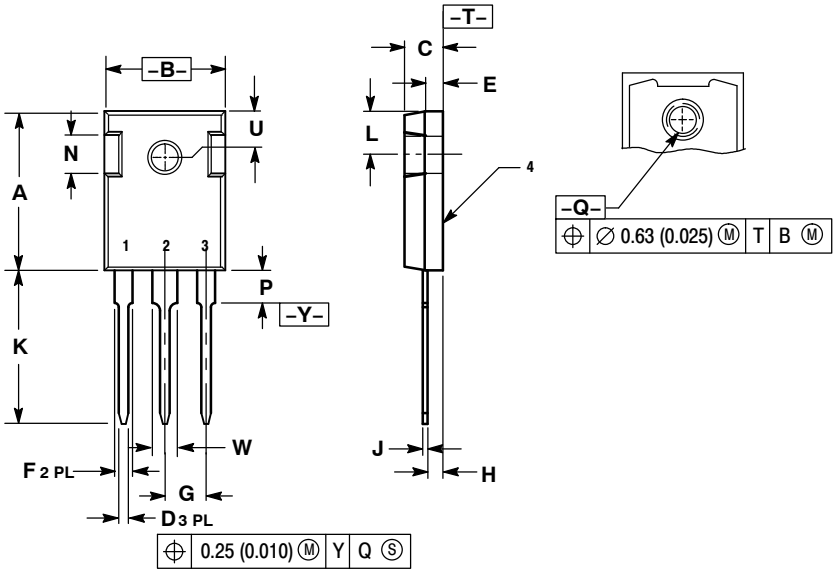


Figure 18. Total Harmonic Distortion Test Circuit

PACKAGE DIMENSIONS

TO−247
CASE 340L−02
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	20.32	21.08	0.800	8.30
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	---	4.50	---	0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

ON Semiconductor and ON are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. “Typical” parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including “Typicals” must be validated for each customer application by customer’s technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative